

FEATURES

44V Supply Maximum Rating
 V_{SS} to V_{DD} Analog Signal Range
Single/Dual Supply Specifications
Wide Supply Ranges (10.8V to 16.5V)
Microprocessor Compatible (100ns \overline{WR} Pulse)
Extended Plastic Temperature Range
 (-40°C to +85°C)
Low Leakage (20pA typ)
Low Power Dissipation (28mW max)
Available in DIP, SOIC, PLCC and LCCC Packages
Superior Alternative to:
 DG526
 DG527

GENERAL DESCRIPTION

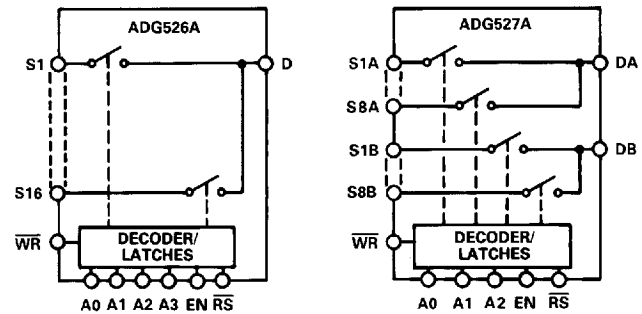
The ADG526A and ADG527A are CMOS monolithic analog multiplexers with 16 channels and dual 8 channels respectively. On-chip latches facilitate microprocessor interfacing. The ADG526A switches one of 16 inputs to a common output depending on the state of four binary addresses and an enable input. The ADG527A switches one of 8 differential inputs to a common differential output depending on the state of three binary addresses and an enable input. Both devices have TTL and 5V CMOS logic compatible digital inputs.

The ADG526A and ADG527A are designed on an enhanced LC²MOS process which gives an increased signal capability of V_{SS} to V_{DD} and enables operation over a wide range of supply voltages. The devices can comfortably operate anywhere in the 10.8V to 16.5V single or dual supply range. These multiplexers also feature high switching speeds and low R_{ON} .

REV. A

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FUNCTIONAL BLOCK DIAGRAMS



PRODUCT HIGHLIGHTS

- Single/Dual Supply Specifications with a Wide Tolerance:**
 The devices are specified in the 10.8V to 16.5V range for both single and dual supplies.
- Easily Interfaced:**
 The ADG526A and ADG527A can be easily interfaced with microprocessors. The \overline{WR} signal latches the state of the Address control lines and the Enable line. The \overline{RS} signal clears both the address and enable data in the latches resulting in no output (all switches off). \overline{RS} can be tied to the microprocessor reset pin.
- Extended Signal Range:**
 The enhanced LC²MOS processing results in a high breakdown and an increased analog signal range of V_{SS} to V_{DD} .
- Break-Before-Make Switching:**
 Switches are guaranteed break-before-make so that input signals are protected against momentary shorting.
- Low Leakage:**
 Leakage currents in the range of 20pA make these multiplexers suitable for high precision circuits.

ADG526A/ADG527A—SPECIFICATIONS

Dual Supply ($V_{DD} = +10.8V$ to $+16.5V$, $V_{SS} = -10.8V$ to $-16.5V$ unless otherwise noted.)

Parameter	ADG526A ADG527A K Version		ADG526A ADG527A B Version		ADG526A ADG527A T Version		Units	Comments
	+25°C	-40°C to +85°C	+25°C	-40°C to +85°C	+25°C	-55°C to +125°C		
ANALOG SWITCH								
Analog Signal Range	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V min V max	
R_{ON}	280 450 300	600 400	280 450 300	600 400	280 450 300	400	Ω typ Ω max Ω max	-10V \leq V_S \leq +10V, $I_{DS} = 1mA$; Test Circuit 1 $V_{DD} = 15V(\pm 10\%)$, $V_{SS} = -15V(\pm 10\%)$ $V_{DD} = 15V(\pm 5\%)$, $V_{SS} = -15V(\pm 5\%)$ -10V \leq V_S \leq +10V, $I_{DS} = 1mA$
R_{ON} Drift	0.6		0.6		0.6		%/°C typ	-10V \leq V_S \leq +10V, $I_{DS} = 1mA$
R_{ON} Match	5		5		5		% typ	-10V \leq V_S \leq +10V, $I_{DS} = 1mA$
I_S (OFF), Off Input Leakage	0.02 1	50	0.02 1	50	0.02 1	50	nA typ nA max	$V_1 = \pm 10V$, $V_2 = \mp 10V$; Test Circuit 2
I_D (OFF), Off Output Leakage	0.04 1	200	0.04 1	200	0.04 1	200	nA typ nA max nA max	$V_1 = \pm 10V$, $V_2 = \mp 10V$; Test Circuit 3
ADG526A	1	100	1	100	1	100		
ADG527A	1	100	1	100	1	100		
I_D (ON), On Channel Leakage	0.04 1	200	0.04 1	200	0.04 1	200	nA typ nA max nA max	$V_1 = \pm 10V$, $V_2 = \mp 10V$; Test Circuit 4
ADG526A	1	100	1	100	1	100		
ADG527A	1	100	1	100	1	100		
I_{DIFF} , Differential Off Output Leakage (ADG527A only)		25		25		25	nA max	$V_1 = \pm 10V$, $V_2 = \mp 10V$; Test Circuit 5
DIGITAL CONTROL								
V_{INH} , Input High Voltage		2.4		2.4		2.4	V min	
V_{INL} , Input Low Voltage		0.8		0.8		0.8	V max	
I_{INL} or I_{INH}		1		1		1	μA max	$V_{IN} = 0$ to V_{DD}
C_{IN} Digital Input Capacitance	8		8		8		pF max	
DYNAMIC CHARACTERISTICS¹								
$t_{TRANSITION}$	200 300	400	200 300	400	200 300	400	ns typ ns max	$V_1 = \pm 10V$, $V_2 = \mp 10V$; Test Circuit 6
t_{OPEN}	50 25	10	50 25	10	50 25	10	ns typ ns min	Test Circuit 7
$t_{ON}(EN, \overline{WR})$	200 300	400	200 300	400	200 300	400	ns typ ns max	Test Circuits 8 and 9
$t_{OFF}(EN, \overline{RS})$	200 300	400	200 300	400	200 300	400	ns typ ns max	Test Circuits 8 and 10
t_W Write Pulse Width	100	120	100	120	100	130	ns min	See Figure 1
t_S Address, Enable Setup Time		100		100		100	ns min	See Figure 1
t_H Address, Enable Hold Time		10		10		10	ns min	See Figure 1
t_{RS} Reset Pulse Width		100		100		100	ns min	See Figure 2
OFF Isolation	68 50		68 50		68 50		dB typ dB min	$V_{EN} = 0.8V$, $R_L = 1k\Omega$, $C_L = 15pF$, $V_S = 7V$ rms, $f = 100kHz$
C_S (OFF)	5		5		5		pF typ	$V_{EN} = 0.8V$
C_D (OFF)								
ADG526A	44		44		44		pF typ	$V_{EN} = 0.8V$
ADG527A	22		22		22		pF typ	
Q_{INJ} , Charge Injection	4		4		4		pC typ	$R_S = 0\Omega$, $V_S = 0V$; Test Circuit 11
POWER SUPPLY								
I_{DD}	0.6	1.5	0.6	1.5	0.6	1.5	mA typ mA max	$V_{IN} = V_{INL}$ or V_{INH}
I_{SS}	20	0.2	20	0.2	20	0.2	μA typ mA max	$V_{IN} = V_{INL}$ or V_{INH}
Power Dissipation	10	28	10	28	10	28	mW typ mW max	

NOTE

¹Sample tested at +25°C to ensure compliance.

Specifications subject to change without notice.

Single Supply ($V_{DD} = +10.8V$ to $+16.5V$, $V_{SS} = GND = 0V$ unless otherwise noted.)

Parameter	ADG526A ADG527A K Version		ADG526A ADG527A B Version		ADG526A ADG527A T Version		Units	Comments
	+25°C	-40°C to +85°C	+25°C	-40°C to +85°C	+25°C	-55°C to +125°C		
ANALOG SWITCH								
Analogue Signal Range	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V_{SS} V_{DD}	V min V max	
R_{ON}	500	1000	500	1000	500	1000	Ω typ Ω max	$0V \leq V_S \leq +10V$, $I_{DS} = 0.5mA$; Test Circuit 1
R_{ON} Drift	0.6		0.6		0.6		%/°C typ	$0V \leq V_S \leq +10V$, $I_{DS} = 0.5mA$
R_{ON} Match	5		5		5		% typ	$0V \leq V_S \leq +10V$, $I_{DS} = 0.5mA$
I_S (OFF), Off Input Leakage	0.02 1	50	0.02 1	50	0.02 1	50	nA typ nA max	$V_1 = +10V/0V$, $V_2 = 0V/+10V$; Test Circuit 2
I_D (OFF), Off Output Leakage	0.04 1	200	0.04 1	200	0.04 1	200	nA typ nA max	$V_1 = +10V/0V$, $V_2 = 0V/+10V$; Test Circuit 3
ADG526A	1	100	1	100	1	100	nA max	
ADG527A	1	100	1	100	1	100	nA max	
I_D (ON), On Channel Leakage	0.04 1	200	0.04 1	200	0.04 1	200	nA typ nA max	$V_1 = +10V/0V$, $V_2 = 0V/+10V$; Test Circuit 4
ADG526A	1	200	1	200	1	200	nA max	
ADG527A	1	100	1	100	1	100	nA max	
I_{DIFF} , Differential Off Output Leakage (ADG527A only)		25		25		25	nA max	$V_1 = +10V/0V$, $V_2 = 0V/+10V$; Test Circuit 5
DIGITAL CONTROL								
V_{INH} , Input High Voltage		2.4		2.4		2.4	V min	
V_{INL} , Input Low Voltage		0.8		0.8		0.8	V max	
I_{INL} or I_{INH}		1		1		1	μA max	$V_{IN} = 0$ to V_{DD}
C_{IN} Digital Input Capacitance	8		8		8		pF max	
DYNAMIC CHARACTERISTICS¹								
$t_{TRANSITION}$	300 450	600	300 450	600	300 450	600	ns typ ns max	$V_1 = +10V/0V$, $V_2 = 0V/+10V$; Test Circuit 6
t_{OPEN}	50		50		50		ns typ	Test Circuit 7
	25	10	25	10	25	10	ns min	
t_{ON} (EN, \overline{WR})	250 450	600	250 450	600	250 450	600	ns typ ns max	Test Circuits 8 and 9
t_{OFF} (EN, \overline{RS})	250 450	600	250 450	600	250 450	600	ns typ ns max	Test Circuits 8 and 10
t_W Write Pulse Width	100	120	100	120	100	130	ns min	See Figure 1
t_S Address, Enable Setup Time		100		100		100	ns min	See Figure 1
t_H Address, Enable Hold Time		10		10		10	ns min	See Figure 1
t_{RS} Reset Pulse Width		100		100		100	ns min	See Figure 2
OFF Isolation	68 50		68 50		68 50		dB typ dB min	$V_{EN} = 0.8V$, $R_L = 1k\Omega$, $C_L = 15pF$, $V_S = 3.5V$ rms, $f = 100kHz$
C_S (OFF)	5		5		5		pF typ	$V_{EN} = 0.8V$
C_D (OFF)	44		44		44		pF typ	$V_{EN} = 0.8V$
ADG526A	22		22		22		pF typ	
ADG527A	4		4		4		pC typ	$R_S = 0\Omega$, $V_S = 0V$; Test Circuit 11
Q_{INJ} , Charge Injection	4		4		4		pC typ	
POWER SUPPLY								
I_{DD}	0.6	1.5	0.6	1.5	0.6	1.5	mA typ mA max	$V_{IN} = V_{INL}$ or V_{INH}
Power Dissipation	11	25	11	25	11	25	mW typ mW max	

NOTE

¹Sample tested at +25°C to ensure compliance.
Specifications subject to change without notice.

TIMING DIAGRAMS

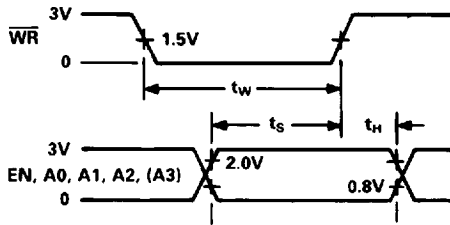


Figure 1.

Figure 1 shows the timing sequence for latching the switch address and enable inputs. The latches are level sensitive; therefore, while \overline{WR} is held low, the latches are transparent and the switches respond to the address and enable inputs. This input data is latched on the rising edge of \overline{WR} .

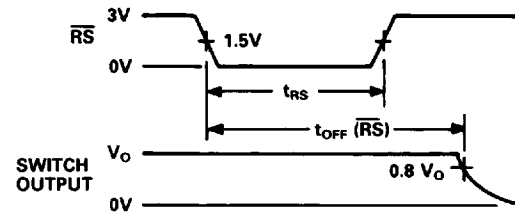


Figure 2.

Figure 2 shows the Reset Pulse Width, t_{RS} , and Reset Turn-off Time, $t_{OFF}(\overline{RS})$.

Note: All digital input signals rise and fall times measured from 10% to 90% of 3V. $t_R = t_F = 20\text{ns}$.

ABSOLUTE MAXIMUM RATINGS*

($T_A = +25^\circ\text{C}$ unless otherwise noted)

V_{DD} to V_{SS}	44V
V_{DD} to GND	25V
V_{SS} to GND	-25V
Analog Inputs ¹	
Voltage at S, D	$V_{SS} - 2\text{V}$ to $V_{DD} + 2\text{V}$ or 20mA, Whichever Occurs First
Continuous Current, S or D	20mA
Pulsed Current S or D	
1ms Duration, 10% Duty Cycle	40mA
Digital Inputs ¹	
Voltage at A, EN, \overline{WR} , \overline{RS}	$V_{SS} - 4\text{V}$ to $V_{DD} + 4\text{V}$ or 20mA, Whichever Occurs First
Power Dissipation (Any Package)	
Up to $+75^\circ\text{C}$	470mW
Derates above $+75^\circ\text{C}$ by	6mW/ $^\circ\text{C}$

Operating Temperature

Commerical (K Version)	-40°C to $+85^\circ\text{C}$
Industrial (B Version)	-40°C to $+85^\circ\text{C}$
Extended (T Version)	-55°C to $+125^\circ\text{C}$
Storage Temperature Range	-65°C to $+150^\circ\text{C}$
Lead Temperature (Soldering, 10sec)	$+300^\circ\text{C}$

NOTE

¹Overvoltage at A, EN, \overline{WR} , \overline{RS} , S or D will be clamped by diodes. Current should be limited to the maximum rating above.

*COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CAUTION:

ESD (electrostatic discharge) sensitive device. The digital control inputs are diode protected; however, permanent damage may occur on unconnected devices subject to high energy electrostatic fields. Unused devices must be stored in conductive foam or shunts. The protective foam should be discharged to the destination socket before devices are inserted.



ORDERING GUIDE

Model ¹	Temperature Range	Package Option ²
ADG526AKN	-40°C to $+85^\circ\text{C}$	N-28
ADG526AKR	-40°C to $+85^\circ\text{C}$	R-28
ADG526AKP	-40°C to $+85^\circ\text{C}$	P-28A
ADG526ABQ	-40°C to $+85^\circ\text{C}$	Q-28
ADG526ATQ ³	-55°C to $+125^\circ\text{C}$	Q-28
ADG526ATE ³	-55°C to $+125^\circ\text{C}$	E-28A
ADG527AKN	-40°C to $+85^\circ\text{C}$	N-28
ADG527AKR	-40°C to $+85^\circ\text{C}$	R-28
ADG527AKP	-40°C to $+85^\circ\text{C}$	P-28A
ADG527ABQ	-40°C to $+85^\circ\text{C}$	Q-28
ADG527ATQ ³	-55°C to $+125^\circ\text{C}$	Q-28
ADG527ATE ³	-55°C to $+125^\circ\text{C}$	E-28A

NOTES

¹To order MIL-STD-883, Class B processed parts, add /883B to part number. See Analog Devices Military Products Databook (1990) for military data.

²E = Leadless Ceramic Chip Carrier; N = Narrow Plastic DIP; P = Plastic Leaded Chip Carrier; Q = Cerdip; R = 0.3" Small Outline IC (SOIC).

³Standard Military Drawing (SMD) assigned by DESC. SMD numbers are

5962-89710013X (ADG526ATE/883B)
5962-8971001XX (ADG526ATQ/883B)
5962-89710023X (ADG527ATE/883B)
5962-8971002XX (ADG527ATQ/883B)

TRUTH TABLES

A3	A2	A1	A0	EN	WR	RS	ON SWITCH
X	X	X	X	X	1	1	Retains Previous Switch Condition
X	X	X	X	X	X	0	NONE (Address and Enable Latches Cleared)
X	X	X	X	0	0	1	NONE
0	0	0	0	1	0	1	1
0	0	0	1	1	0	1	2
0	0	1	0	1	0	1	3
0	0	1	1	1	0	1	4
0	1	0	0	1	0	1	5
0	1	0	1	1	0	1	6
0	1	1	0	1	0	1	7
0	1	1	1	1	0	1	8
1	0	0	0	1	0	1	9
1	0	0	1	1	0	1	10
1	0	1	0	1	0	1	11
1	0	1	1	1	0	1	12
1	1	0	0	1	0	1	13
1	1	0	1	1	0	1	14
1	1	1	0	1	0	1	15
1	1	1	1	1	0	1	16

X = Don't Care

ADG526A

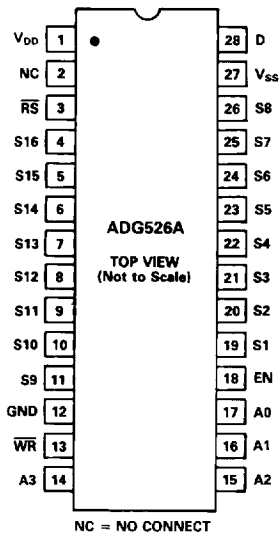
A2	A1	A0	EN	WR	RS	ON SWITCH PAIR
X	X	X	X	1	1	Retains Previous Switch Condition
X	X	X	X	X	0	NONE (Address and Enable Latches Cleared)
X	X	X	0	0	1	NONE
0	0	0	1	0	1	1
0	0	1	1	0	1	2
0	1	0	1	0	1	3
0	1	1	1	0	1	4
1	0	0	1	0	1	5
1	0	1	1	0	1	6
1	1	0	1	0	1	7
1	1	1	1	0	1	8

X = Don't Care

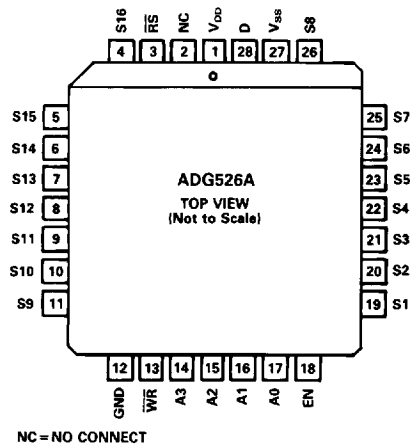
ADG527A

PIN CONFIGURATIONS

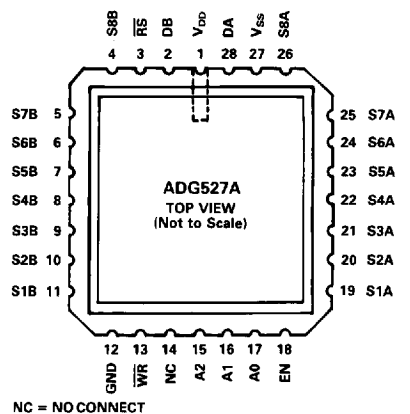
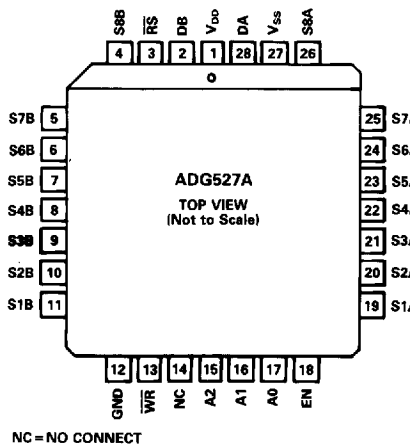
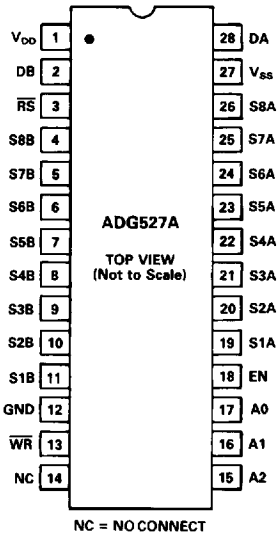
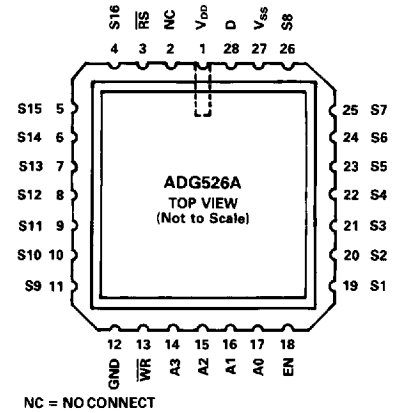
DIP, SOIC



LCCC



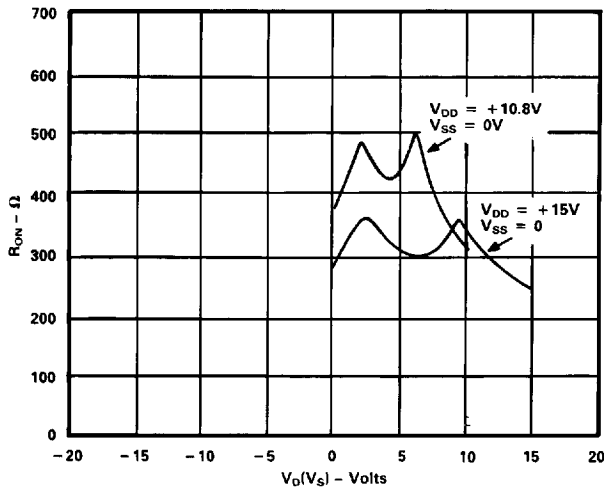
PLCC



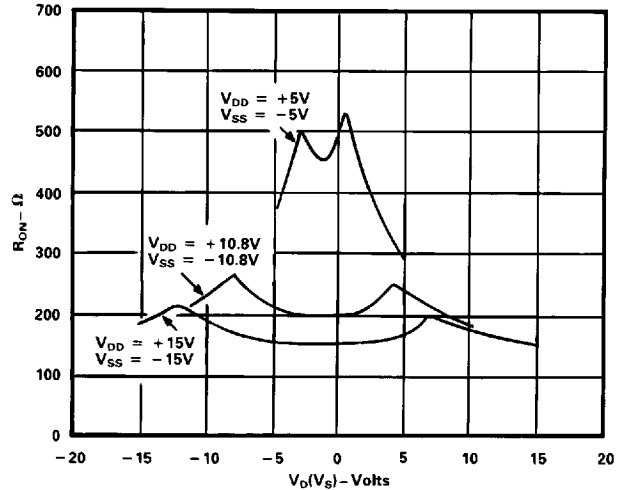
ADG526A/ADG527A

Typical Performance Characteristics

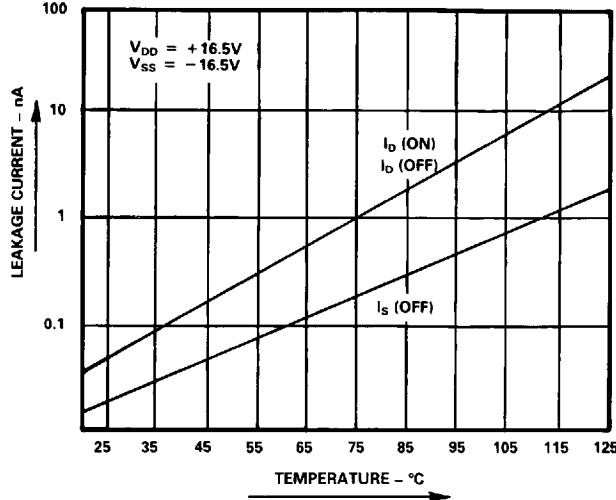
The multiplexers are guaranteed functional with reduced single or dual supplies down to 4.5V.



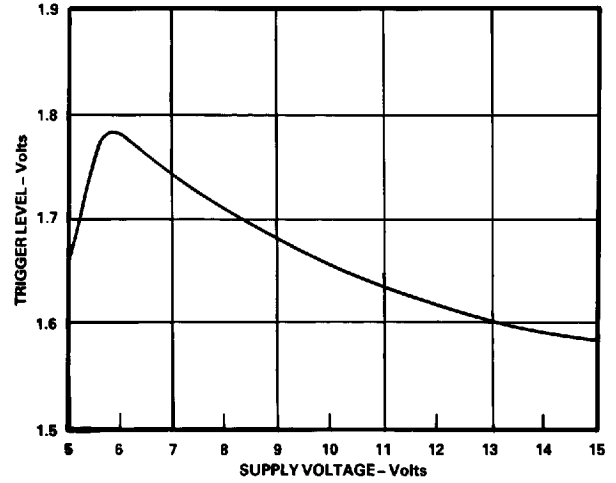
R_{ON} as a Function of $V_D(V_S)$: Dual Supply Voltage, $T_A = +25^\circ C$



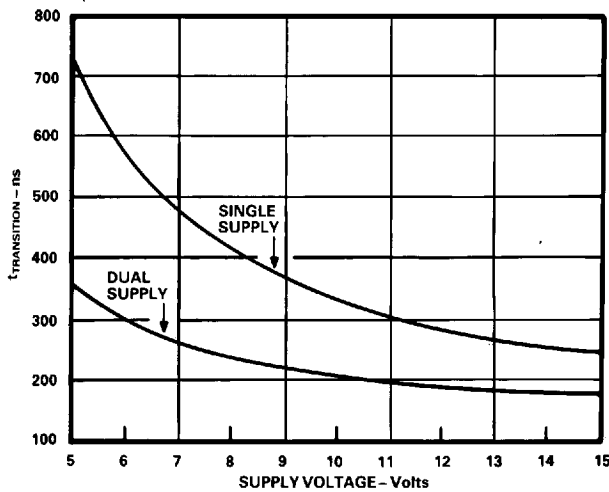
R_{ON} as a Function of $V_D(V_S)$: Single Supply Voltage, $T_A = +25^\circ C$



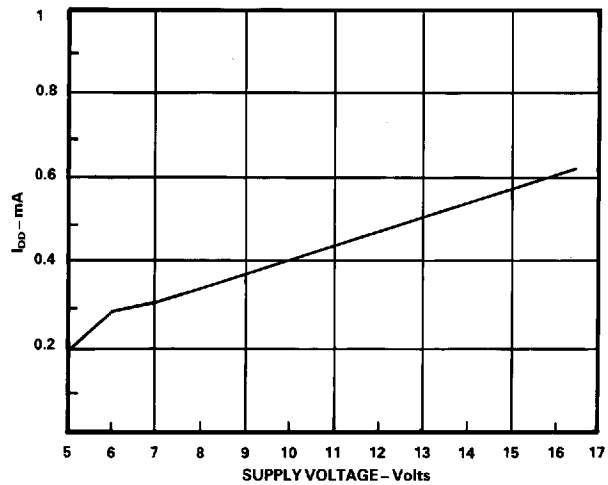
Leakage Current as a Function of Temperature
(Note: Leakage Currents Reduce as the Supply Voltages Reduce)



Trigger Levels vs. Power Supply Voltage, Dual or Single Supply, $T_A = +25^\circ C$



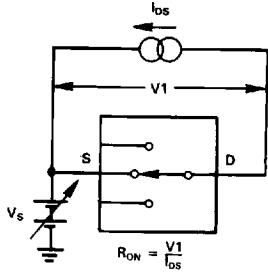
$t_{TRANSITION}$ vs. Supply Voltage: Dual and Single Supplies, $T_A = +25^\circ C$
(Note: For V_{DD} and $|V_{SS}| < 10V$; $V1 = V_{DD}/V_{SS}$, $V2 = V_{SS}/V_{DD}$. See Test Circuit 6)



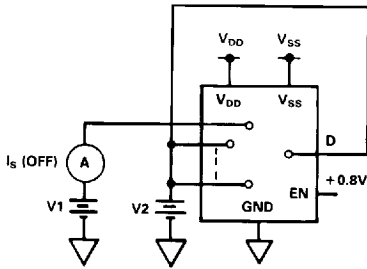
I_{bD} vs. Supply Voltage: Dual or Single Supply, $T_A = +25^\circ C$

Test Circuits—ADG526A/ADG527A

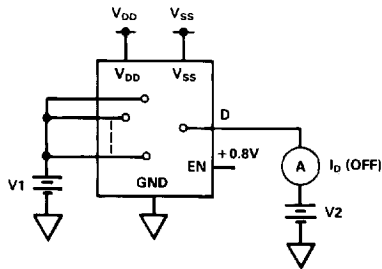
TEST CIRCUIT 1 R_{ON}



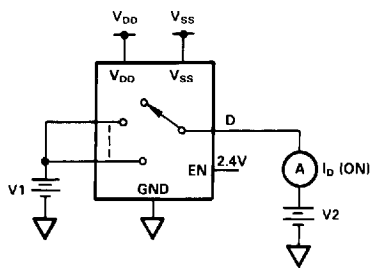
TEST CIRCUIT 2 I_S (OFF)



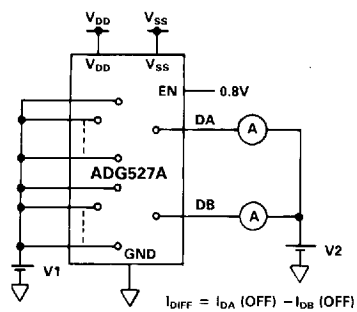
TEST CIRCUIT 3 I_D (OFF)



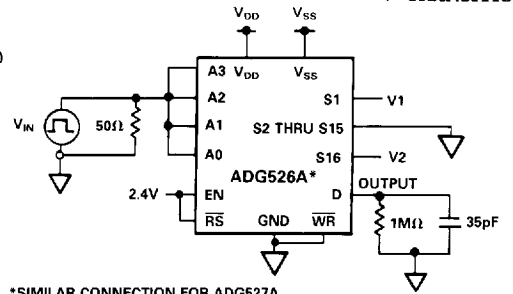
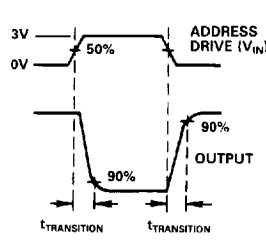
TEST CIRCUIT 4 I_D (ON)



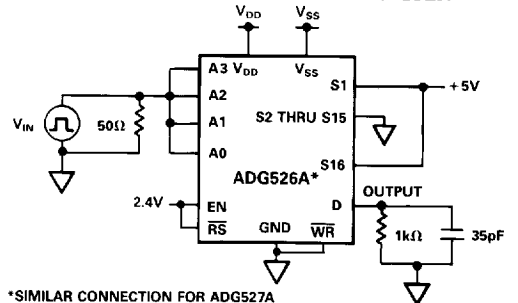
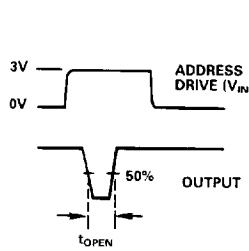
TEST CIRCUIT 5 I_{DIFF}



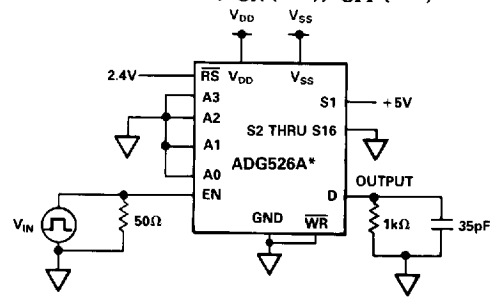
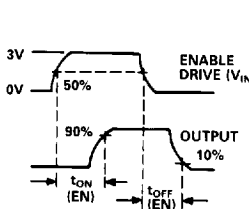
TEST CIRCUIT 6 SWITCHING TIME OF MULTIPLEXER, $t_{TRANSITION}$



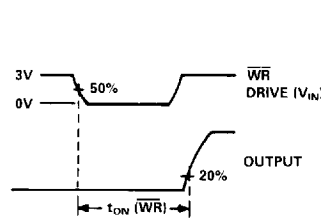
TEST CIRCUIT 7 BREAK-BEFORE-MAKE DELAY, t_{OPEN}



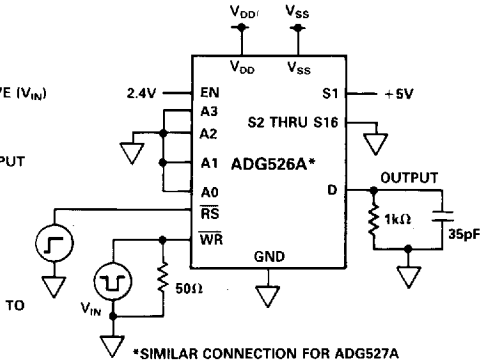
TEST CIRCUIT 8 ENABLE DELAY, t_{ON} (EN), t_{OFF} (EN)



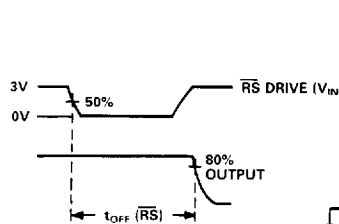
TEST CIRCUIT 9 WRITE TURN-ON TIME, t_{ON} (\overline{WR})



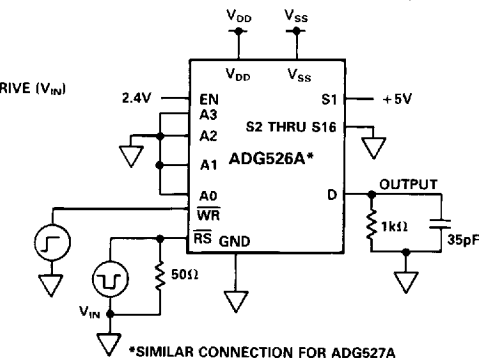
NOTE: DEVICE MUST BE RESET PRIOR TO APPLYING \overline{WR} PULSE



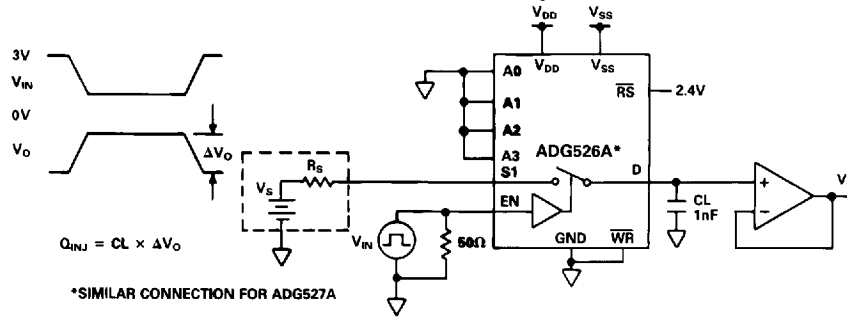
TEST CIRCUIT 10 RESET TURN-OFF TIME, t_{OFF} (\overline{RS})



NOTE: \overline{WR} MUST BE PULSED LOW PRIOR TO APPLYING \overline{RS} PULSE.



TEST CIRCUIT 11 CHARGE INJECTION



TERMINOLOGY

- R_{ON} Ohmic resistance between terminals D and S
- R_{ON} Match Difference between the R_{ON} of any two channels
- R_{ON} Drift Change in R_{ON} versus temperature
- I_S (OFF) Source terminal leakage current when the switch is off
- I_D (OFF) Drain terminal leakage current when the switch is off
- I_D (ON) Leakage current that flows from the closed switch into the body
- V_S (V_D) Analog voltage on terminal S or D
- C_S (OFF) Channel input capacitance for "OFF" condition
- C_D (OFF) Channel output capacitance for "OFF" condition
- C_{IN} Digital input capacitance
- t_{ON} (EN) Delay time between the 50% and 90% points of the digital input and switch "ON" condition

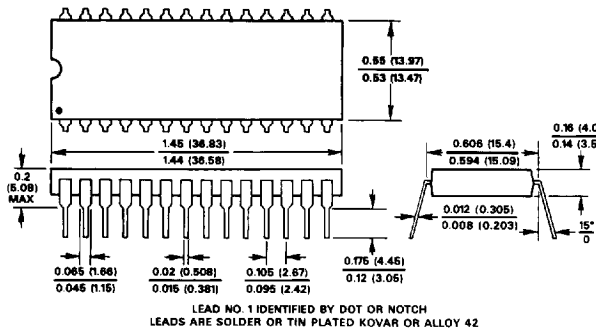
- t_{OFF} (EN) Delay time between the 50% and 10% points of the digital input and switch "OFF" condition
- $t_{TRANSITION}$ Delay time between the 50% and 90% points of the digital inputs and switch "ON" condition when switching from one address state to another
- t_{OPEN} "OFF" time measured between 50% points of both switches when switching from one address state to another
- V_{INL} Maximum input voltage for Logic "0"
- V_{INH} Minimum input voltage for Logic "1"
- I_{INL} (I_{INH}) Input current of the digital input
- V_{DD} Most positive voltage supply
- V_{SS} Most negative voltage supply
- I_{DD} Positive supply current
- I_{SS} Negative supply current

MECHANICAL INFORMATION

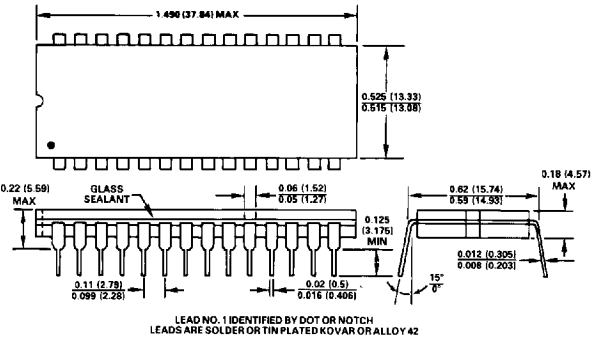
OUTLINE DIMENSIONS

Dimension shown in inches and (mm).

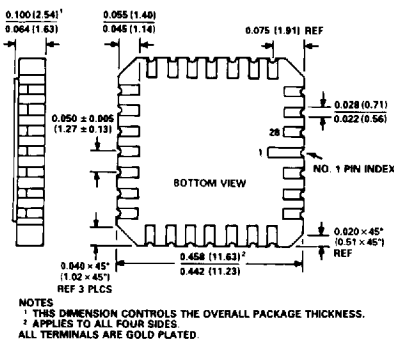
28-Pin Plastic DIP (Suffix N)



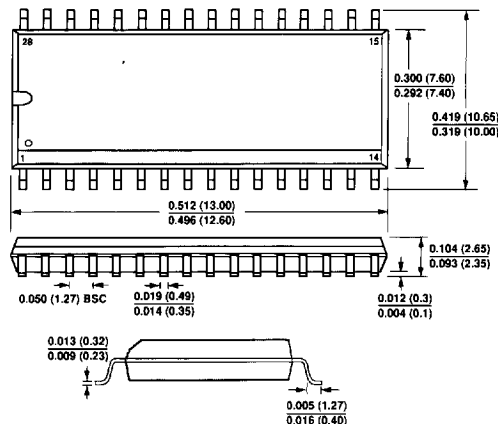
28-Pin Cerdip (Suffix Q)



28-Terminal Leadless Ceramic Chip Carrier (Suffix E)



28-Pin SOIC (R) Package



28-Terminal Plastic Leaded Chip Carrier (Suffix P)

